

METHOD FOR CHEMICAL MECHANICAL POLISHING SILICON WAFERS

Abstract of the Disclosure

A method for polishing a silicon wafer is provided, comprising: providing a silicon wafer; providing a polishing pad having a polishing layer which is the reaction product of raw material ingredients, including: a polyfunctional isocyanate; and, a curative package; wherein the curative package contains an amine initiated polyol curative and a high molecular weight polyol curative; wherein the polishing layer exhibits a density of greater than 0.4 g/cm^3 ; a Shore D hardness of 5 to 40; an elongation to break of 100 to 450%; and, a cut rate of 25 to 150 $\mu\text{m/hr}$; and, wherein the polishing layer has a polishing surface adapted for polishing the silicon wafer; and, creating dynamic contact between the polishing surface and the silicon wafer.

Fig 1